

ABSTRACT OF THE DISCLOSURE

A magnetic memory device includes first to n-th MTJ devices recording data and first to n-th transistors connected to the first to n-th MTJ devices, respectively. The word line generates a magnetic field to be applied to the first to n-th MTJ devices during a write operation. A read word line is connected to gates of the first to n-th transistors and applies a voltage for turning on the first to n-th transistors during a read operation. A first word line driver is connected to a first end or a second end of the write word line and drives the write word line. A second word line driver is connected to a first end of the read word line and drives the read word line. A second switching circuit selectively connects the second end of the read word line and the second end of the write word line.